



福建省长兴电子有限公司

CHANGXING ELECTRONICS CO., LTD.

福建省将乐县东门新村3号

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石英晶体振荡器产品确认书

Quartz Crystal Oscillator Specification For Approval

产品型号:	2.5×2.0 OSC 40.000000MHz
Model	
客户名称:	
Customer	
客户编号:	
Customer's Part No.	
长兴编号:	4ESC400C0033L
Product No.	
发行日期:	
Issue Date	

承办: 吴丽萍

审核: 林东国

批准: 吕锡昌

内容:

- 1、Features 特点
- 2、Electrical Specifications 电气参数
- 3、Dimensions 外型尺寸
- 4、Test Diagram 测试电路
- 5、Marking 印码
- 6、Reflow Condition 回流焊条件
- 7、Packing 包装 (EIA-481-2)
- 8、Reliability Specifications 可靠性规范
- 9、Material Composition Declaration 产品物质成分表

客户 Conclusion:

☐ Conditional Approval ☐ Full Approval ☐ Reject

会 签 意 见	
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APPROVED BY :

ISSUED DATE :

2.5×2.0×0.8mm SMD Crystal Oscillators CMOS Output / 4E Series

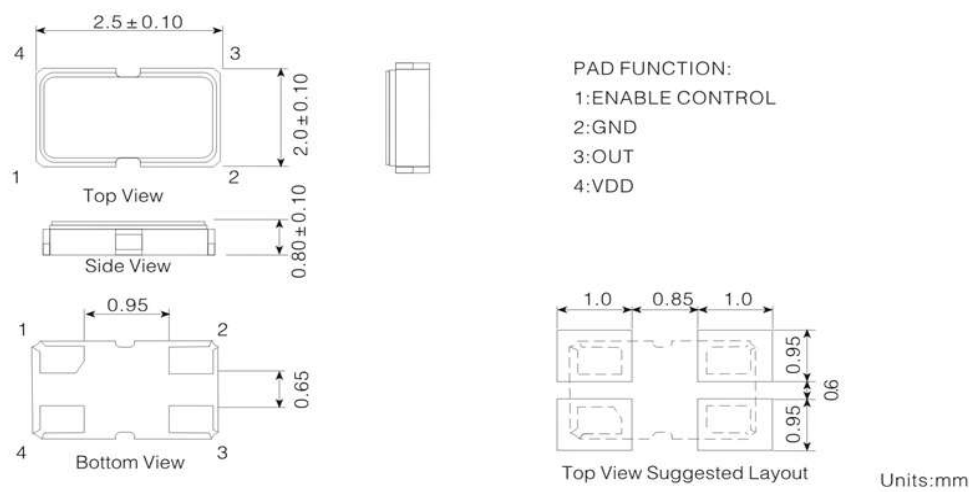
■ Features 特点

- . Ultra Small SMD seam sealed clock crystal oscillator units.
- . For applications in WLAN, Bluetooth, DSC, DSL and other IT product.
- . Tri-state function available.
- . RoHS Compliant / Pb Free.

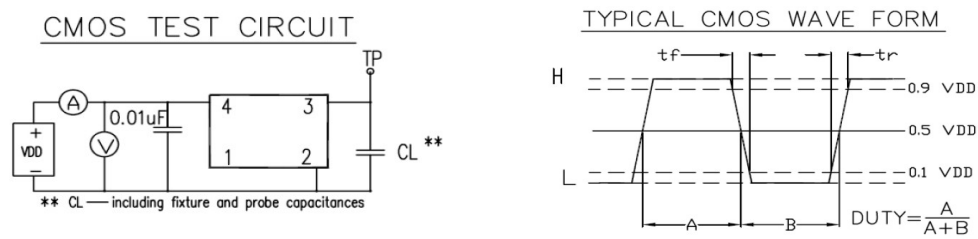
■ Electrical Specifications 电气参数

1、	Nominal Frequency:	40.000000	MHz
2、	Tolerance @ 25 Degree:	±10	ppm
3、	Stability over Operation Temp.:	±20	ppm
4、	Aging:	±3	ppm/year
5、	Operating Temperature Range:	-40~85	°C
6、	Storage Temperature Range:	-55~125	°C
7、	Supply Voltage (Vdd):	1.8V~3.3V	Vdc
8、	Supply Current (Icc):	8	mA max
9、	Output Waveform:	CMOS	
10、	Output Symmetry:	50±10%	
11、	Rise/Fall Time:	5	ns max
12、	Output Voltage VOL:	10%VDD	max
	Output Voltage VOH:	90%VDD	min
13、	Output Load:	15	pF
14、	Output State Control:	Enable/disable	
15、	Enable Voltage High:	70%Vdd	min
	Disable Voltage Low:	30%Vdd	max
16、	Start-up Time:	5	ms max
17、	Standby current:	10	μA max
18、	Phase Jitter(12KHz ~ 20MHz):	3	ps max
19、	Oscillation mode:	Fundamental	
20、	MSL	Level 1	IPC/JEDEC J-STD-033C

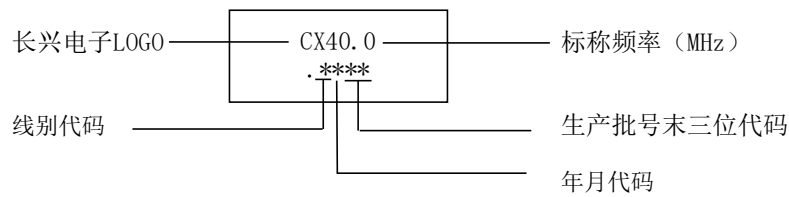
■ Dimensions外型尺寸



■ Test Diagram测试电路



■ Marking印码

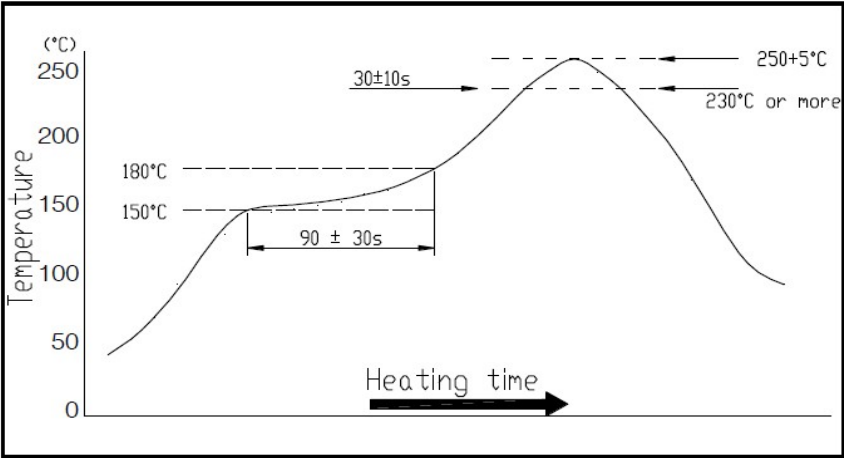


年月代码（四年一个周期）：

年份	月份	一月	二月	三月	四月	五月	六月	七月	八月	九月	十月	十一月	十二月
2023	2027	a	b	c	d	e	f	g	h	j	k	l	m
2024	2028	n	p	q	r	s	t	u	v	w	x	y	z
2025	2029	A	B	C	D	E	F	G	H	J	K	L	M
2026	2030	N	P	Q	R	S	T	U	V	W	X	Y	Z

■ Reflow Condition回流焊条件

Solder profile
Peak: 250+50℃ Soldering zone: 230℃ or more, 30±10s.
Pre-heating zone 1: 150~180℃, 90±30s

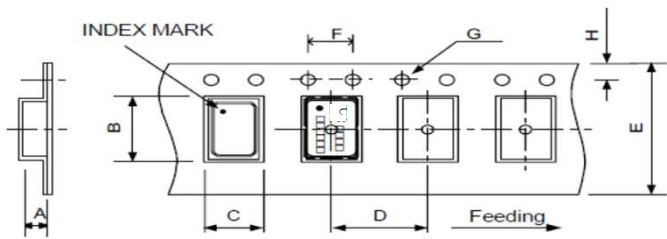


Temperature profile for reflow soldering

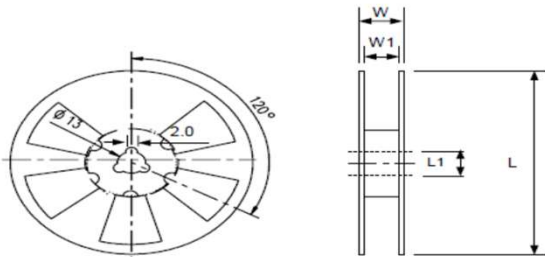
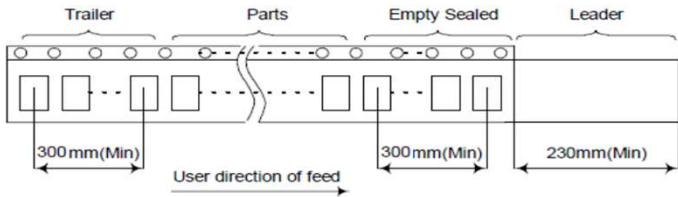
Soldering iron method
Bit temperature: 350±10℃ Application time of soldering iron:3+1 s
For other procedures, refer to IEC 60068-2-20.

■ Packing包装（EIA-481-2）

TAPE (CARRIER) DIMENSIONS



DIMENSIONS	A	B	C	D	E	F	G	H
UNIT : mm	1.20±0.1	2.70±0.1	2.25±0.1	4.00±0.1	8.0±0.2	4.00±0.1	1.55±0.03	1.75±0.1



DIMENSIONS	L	L1	W	W1	Standard Reel Quantity
UNIT : mm	178±1.0	13±0.5	11.5±0.2	8.0±1.0	3,000 pcs per reel (WHITE)

■ Reliability Specifications可靠性规范

This is the quality control and quality assurance and reliability tests performance

data for the 2.5×2.0 OSC 26.000000MHz

Standard test condition (TEMP.: 20±15℃. Relative humidity: 65±20%)

For any discrepancy in GO/NG, test will be done at TEMP. 25±2℃. R.H. 65±5%.

NO	ITEM	SPECIFICATION	TEST METHOD
1	Temperature Cycle (GB/T2423. 22-2002, Method Nb)	Frequency change after test≤±5ppm.	10 cycles from -25° C to 85° C. Measurement taken after DUT being left at room temperature for 24±2 hours.
2	Low Temperature Storage(GB/T 2423. 1-2001, MethodAa)	Frequency change after test≤±5ppm.	Spending 72 hrs at -55° C±3° C constant temperature.Measurement taken after DUT being left at roomtemperature for 24±2 hours.
3	High Temperature Storage(GB/T 2423. 2-2001, MethodBa)	Frequency change after test≤±5ppm.	Spending 72 hrs at 125° C±3° C constant temperature.Measurement taken after DUT being left at roomtemperature for 24±2 hours.
4	Humidity (GB/T 2423. 3-2006, Method Cab)	Frequency change after test≤±5ppm.	Spending 96 hrs at 40 ° C ± 3 ° C, with 90± 3% R.H.Measurement taken after DUT being left at roomtemperature for 24±2 hours.
5	Vibration (GB/T 2423. 10-1995, Method Fc)	Frequency change after test≤±5ppm.	Apply 0.75mm vibration at sweep frequency 10~500 Hz,for 2h. 10 cycles in each direction of 3 axis. Measurementtaken after 1 hour.
6	Shock (GB/T 2423. 5-1995, Method Ea)	Frequency change after test≤±5ppm. No visible damages.	Peak 1000m/s ² , normal width 6ms half sine wave form, 3.7m/s, 3 perpendicular axis of samples, 3 cycles /direction, total 18 cycles. Measurement taken after 1hour.
7	Drop (GB/T 2423. 8-1995, Method Ed)	Frequency change after test≤±5ppm. No visible damages.	Free drop to the wooden plate from 1.0 m heights for 3times.
8	Solderability (GB/T 2423. 28-2005, Method Tc)	Terminals shall be coveredmore then 95% with solder.	In 255 ± 5℃ solder bath for 2 ± 0.5 seconds. There is noneed to do functioned test. 8-12X magnifier.
9	Terminal Strength (JIS-C-6429 Method 1 & 2)	No visible damage	Mount on a glass-epoxy board (100x50x1.6mm), thenbend to 2mm displacement (velocity 1mm/sec) and keepfor 5 seconds. or pulling force 0.5 kg for at least 60seconds.
10	Resistance to SolderingHeat (GB/T 2423. 28-2005, Test Tb Method 1B)	Frequency change after test≤±5ppm.	Passed through the re-flow oven under the followingcondition. Preheat to 150 ° C±5° C for 60 to 120sec, andpeak 265 ° C±5° C for 10s±3sec.Measurement taken afterDUT being left at room temperature for at 24±2 hours.

Material Composition Declaration

材 料 成 份 表

1.PRODUCTION NAME : OSC 2520

2.PRODUCTION WEIGHT(mg) : 13.843

编号 No.	构成部件 Name of Part	部件材质名 Material Name	构成之元素名称 Constituent name	CAS编号 CAS No.	元素百分比 Material Analysis(%)
1	基座 Base	陶瓷 Ceramics	Al ₂ O ₃ Aluminum oxide	1344-28-1	63.88%
			SiO ₂ Silica	14464-46-1	3.79%
			Cr ₂ O ₃ Chromium oxide	1308-38-9	1.29%
			Mo Molybdenum	7439-98-7	1.00%
		Pin	Fe Iron	7440-33-7	9.25%
			Ni Nickel	7439-89-6	8.85%
			Co Cobalt	7440-02-0	4.75%
		焊料 Solder	Ag silver	7440-48-4	2.98%
			Cu Copper	7440-22-4	2.80%
		金属化 Metallization	W Tungsten	7440-50-8	1.04%
		电镀层 Plate	Au Gold	7440-02-0	0.24%
			Ni Nickel	7440-57-5	0.13%
2	外壳 Lid	Kovar	Fe Iron	7439-89-6	54.00%
			Co Cobalt	7440-48-4	17.02%
			Ni Nickel	7440-02-0	28.32%
		Ni (镀层)	Ni Nickel	7440-02-0	0.66%
3	Adhesive	Resin	-	-	100.00%
4	Blank	晶片 Quartz	SiO ₂ Silicon oxide	14808-60-7	100.00%
5	Wire	Gold	Au Gold	7440-57-5	100.00%
6	IC	Ssilicon	Silicon	7440-21-3	100.00%
7	Electrode	电极 Electrode	Ag Silver	7440-22-4	100.00%
8	Epoxy	Conductive Resin	Silver	7440-22-4	74.00%
			Ethyl alcohol	64-17-5	0.60%
			Bisphenol A-epichlorohydrin polymer	25068-38-6	0.60%
			Xylenes (o-, m-, p-isomers)	1330-20-7	0.60%
			Ethylbenzene	100-41-4	0.06%
			Silicone resin	-	8.62%
			Silica	-	8.52%
			Petroleumsolvents	-	7.00%